Monolayer nitrides doped with transition metals as efficient catalysts for water oxidation

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Monolayer Nitrides Doped with Transition Metals as Efficient Catalysts for Water Oxidation: The Singular Role of Nickel

Qihua Liang,[†] Geert Brocks,^{‡,§,||} Xueqing Zhang,^{†,‡} and Anja Bieberle-Hütter^{*,†,‡,||}[†]Electrochemical Materials and Interfaces (EMI), Dutch Institute for Fundamental Energy Research (DIFFER), De Zaale 20, 5612 AJ Eindhoven, The Netherlands[‡]Center for Computational Energy Research (CCER), P.O. Box 513, 5600 MB Eindhoven, The Netherlands[§]Department of Applied Physics, Eindhoven University of Technology, P.O. Box 513, 5600 MB Eindhoven, The Netherlands^{||}Computational Materials Science, Faculty of Science and Technology and MESA+ Institute for Nanotechnology, University of Twente, P.O. Box 217, 7500 AE Enschede, The Netherlands

Supporting Information

ABSTRACT: Exploration of precious-metal-free catalysts for water splitting is of great importance in developing renewable energy conversion and storage technologies. In this paper, on the basis of density functional theory calculations, we reveal the link between the oxygen evolution reaction (OER) activities and the electronic properties of pure and first-row transition-metal (TM)-doped AlN and GaN two-dimensional monolayers. We find that Ni-doped layers are singularly appealing because they lead to a low overpotential (0.4 V). Early TM dopants are not suited for the OER because they bind the intermediate species OH or O too strongly, which leads to very large overpotentials, or no OER activity at all. The late TM dopants Cu and Zn show less or no OER activity as they bind the intermediate species too weakly. Although in many cases the overpotential can be traced back to an OOH intermediate species being adsorbed too weakly compared to an OH species, the Ni dopant breaks this rule by stabilizing the OOH adsorbant. The stabilization can be correlated with a switch from a high-spin to a low-spin state of the dopant atom. This ability to change spin states offers an exciting ingredient for the design of OER catalysts.

INTRODUCTION

The global greenhouse gas emission and environmental pollution problems require the development of renewable and green energy systems. Electrochemical and photoelectrochemical splitting of water into hydrogen and oxygen present promising approaches to a green and renewable energy conversion and storage technology.^{1–3} Water splitting comprises two half reactions: the cathodic hydrogen evolution reaction and the anodic oxygen evolution reaction (OER). The OER is considered to be the main bottleneck because the reaction requires a high overpotential, which limits the efficiency of the energy conversion.^{4,5} Until now, the most effective electrocatalysts known for the OER are oxides of platinum group transition metals (TMs) such as Ir or Ru.^{6,7} Such electrocatalysts cannot be used in large-scale applications, however, as these TMs are scarce and costly. Over the last few decades, oxides of earth-abundant TMs have also been widely studied as alternatives, such as Fe₂O₃,^{8–11} TiO₂,^{12,13} WO₃,^{14,15} Co₃O₄,^{16,17} and MnO₂.^{18,19} Although they are cheap and have

a high chemical stability, these TM oxides suffer from high OER overpotentials and low catalytic activities.^{20–22} In addition, as the conductivity of such materials is low, transport of charge carriers becomes a problem. In other words, there is plenty of room for improvement of platinum-group-free TM compounds for OER (photo)electrocatalysis.

It is well known that reducing sizes to the nanometer regime can alter and improve the catalytic properties of materials. Size reduction is recognized as an effective path to improve the electrochemical performance for water splitting.^{23,24} Two-dimensional (2D) materials are special, as they naturally come with a reduction of size in one dimension, which facilitates charge transport across the material. At the same time, 2D materials maintain a high surface area, which is important as OER activity critically depends on the number of active surface

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sites. Since the discovery of the prototype 2D material graphene,²⁵ several 2D materials have been studied regarding OER activity.^{2,23,26} Among these is TM and nitrogen co-doped graphene, where in computational studies, it is claimed that the OER electrocatalytic activity can be comparable to that of platinum group TM oxides.^{27–29} Similarly, the TM-doped 2D materials C_2N and $g-C_3N_4$ have been proposed as efficient OER catalysts.^{30,31} However, in all of these graphene-like C_xN_y materials, the TM and nitrogen dopant atoms need to be in specific (e.g., porphyrin-like) configurations to express their catalytic activity, and it is difficult to foresee how these can be synthesized controllably on a large scale.

In this paper, we suggest an alternative approach, starting from the graphene-like nitrides AlN and GaN. These 2D materials have been studied computationally^{32–34} and realized experimentally in recent years. 2D AlN has been grown on Ag(111),³⁵ and 2D GaN has been synthesized using graphene encapsulation.³⁶ AlN- and GaN-based heterostructures have been investigated computationally as potential candidates for water splitting.^{37–39} It is unclear whether such TM-free compounds can show sufficient catalytic activity. However, just like in their three-dimensional counterparts,^{40–42} it should be possible to introduce TM atoms in 2D group III–V monolayer materials by substitutional doping, that is, TM atoms replacing the Ga or Al cations in the lattice. First-row TM-doped systems have been widely studied as OER catalysts, and the activity of the TM dopant depends on the systems, in particular, on the electronic configuration of the dopant atom, and on the interaction of the dopant atom with the surrounding lattice. In different systems, the TMs show different OER activity.^{43–47} Such substitutional doping should be easier to achieve than the special TM configurations required for the graphene-like C_xN_y compounds, for instance. In this paper, we have carried out a systematic study of the catalytic activity on the OER of first-row TM-doped monolayers of AlN and GaN.

THEORETICAL METHODS

All calculations are performed within density functional theory (DFT), using the projector-augmented wave approach, as implemented in the Vienna Ab initio Simulation Package (VASP).^{48–50} The electronic exchange–correlation energy is treated within the generalized gradient approximation (GGA) as parameterized by Perdew–Burke–Ernzerhof.⁵¹ To test the stability of the spin states found for the (adsorbed species on the) TM-doped AlN and GaN, we apply the GGA + U method, where the on-site electron–electron Coulomb interaction U is treated within the Dudarev et al. approach.⁵² This is discussed in the Supporting Information.

We construct a 4×4 in-plane supercell of XN ($X = \text{Al}$ or Ga) in a planar honeycomb lattice, see Figure 1a. To mimic TM doping, one Ga or Al atom in this supercell is replaced by a TM atom. The intermediate species active in the OER are then adsorbed at this TM site. In the direction perpendicular to the XN plane, the XN layers are separated by a vacuum spacing of 15 Å to prevent the interaction between periodical images, see Figure 1b, where we also use a dipole correction.⁵³ All atoms in the supercell are relaxed until the maximum force on each atom is less than 0.02 eV/Å, and the energy convergence criterion is set to 1×10^{-4} eV.

A plane wave basis with a kinetic energy cutoff of 500 eV and a Monkhorst–Pack⁵⁴ grid of $4 \times 4 \times 1$ k -points are used for the geometry optimization. A finer $10 \times 10 \times 1$ k -point

Figure 1. Top (a) and side (b) views of TM-doped hexagonal monolayer nitrides XN in a 4×4 supercell ($X = \text{Al}$ and Ga); PDOS of (c) AlN and (d) GaN monolayers. The top of the valence band is set to zero energy.

mesh is used to calculate the density of states (DOS). In order to describe possible van der Waals interactions between adsorbates and substrate, Grimme's semiempirical DFT-D3 scheme of dispersion correction is used.⁵⁵ In all calculations, we apply spin polarization.

As a test, we analyze the electronic structure of pristine planar AlN and GaN monolayers. The calculated projected densities of states (PDOS) are shown in Figure 1c,d. Both AlN and GaN are large band gap semiconductors, with DFT band gaps of 2.96 and 1.78 eV, respectively, which agree with previous studies.^{34,37} The top of the valence band is dominated by contributions from nitrogen atoms, while the bottom of the conduction band has a mixed cation (Al or Ga)–anion character.

In calculating the total energies of molecules and adsorbed species, we correct for the zero-point energies, obtained from the calculated frequencies (ν_i) of all vibrations of the atoms in the supercell

$$\text{ZPE} = \sum_i \frac{1}{2} h \nu_i \quad (1)$$

where h is Planck's constant. The vibrational contribution to the entropy S of molecules and adsorbed species can be calculated from these frequencies as⁵⁶

$$S = k_B \sum_i \left[\frac{h \nu_i}{k_B T (e^{h \nu_i / k_B T} - 1)} - \ln(1 - e^{-h \nu_i / k_B T}) \right] \quad (2)$$

with k_B the Boltzmann constant and T the temperature.⁵⁷ In this paper, we set $T = 300$ K. We used gas-phase H_2O at 0.035 bar as the reference state because at this pressure, gas-phase H_2O is in equilibrium with liquid water at 300 K.⁵⁸ Entropies

Figure 2. (a) Calculated Gibbs free energy diagrams of pristine and TM-doped AlN and GaN systems. The purple-shaded fields indicate the overpotential-determining reaction steps. The values of the overpotential are given in the legends. (b) Summary plot of the overpotential for the different TM dopants. The overpotential-determining reaction steps are represented by different colors.

of the gases H₂, O₂, and H₂O are taken from the ref 58 (see Table S1). In the solid state, volume changes are typically very small, and the small difference between enthalpy and energy is normally neglected.⁴⁶ We have refrained from modeling solvation effects.

RESULTS AND DISCUSSION

Reaction Energies and Overpotentials. In an acidic environment, the OER can be expressed as

We follow the reaction mechanism established by Rossmeisl et al.,⁵⁹ where the OER proceeds in four sequential steps at the same reaction site, each step involving a single electron and proton

Here, * represents the surface; (l) and (g) refer to the liquid and gas phases, respectively; and *OH, *O, and *OOH represent the species adsorbed on the surface. Assuming the standard hydrogen electrode as the reference electrode, we have the equilibrium

at $T = 300$ K, $\text{pH} = 0$, and a hydrogen gas pressure of 1 bar. Assuming this equilibrium, we may then replace the protons plus electrons in reactions 3–7 by hydrogen gas under these

conditions in calculations of the reaction-free energies. Water molecules adsorbed on the surface are in equilibrium with liquid water, and oxygen molecules adsorbed on the surface are in equilibrium with oxygen gas under standard conditions. The Gibbs free energies of H₂O and O₂ adsorption are then equal to that of a water molecule in the liquid and an O₂ molecule in the gas, respectively. Note that for microkinetic modeling, one would need to broaden this scope.⁶⁰ The Gibbs free energy of reaction 3 is then 4.92 eV, that is, twice the standard formation energy $\Delta G_{\text{H}_2\text{O}}$ of a H₂O molecule from H₂ and 1/2 O₂. Assuming that each of the four steps 4–7 has the same Gibbs free energy, ΔG_0 , then gives

$$\Delta G_0 = \frac{1}{2}\Delta G_{\text{H}_2\text{O}} = 1.23 \text{ eV} \quad (9)$$

which is the minimum potential required for this reaction to proceed. In reality, the four steps will not have the same Gibbs free energy, which then leads to an overpotential.

For each of these four steps, we calculate the reaction Gibbs free energy as

$$\Delta G_1 = E(*\text{OH}) - E(*) - E_{\text{H}_2\text{O}} + \frac{1}{2}E_{\text{H}_2} + (\Delta\text{ZPE} - T\Delta S)_1 \quad (10)$$

$$\Delta G_2 = E(*\text{O}) - E(*\text{OH}) + \frac{1}{2}E_{\text{H}_2} + (\Delta\text{ZPE} - T\Delta S)_2 \quad (11)$$

$$\Delta G_3 = E(*\text{OOH}) - E(*\text{O}) - E_{\text{H}_2\text{O}} + \frac{1}{2}E_{\text{H}_2} + (\Delta\text{ZPE} - T\Delta S)_3 \quad (12)$$

$$\Delta G_4 = E(*) - E(*\text{OOH}) + E_{\text{O}_2} + \frac{1}{2}E_{\text{H}_2} + (\Delta\text{ZPE} - T\Delta S)_4 \quad (13)$$

ΔG_i , with $i = 1-4$, are the Gibbs free energies associated with the four reactions of eqs 4–7. $E(*)$, $E(*\text{OH})$, $E(*\text{O})$, and $E(*\text{OOH})$ are the calculated total energies of a clean surface and surfaces with a single adsorbed OH, O, and OOH species, respectively. $E_{\text{H}_2\text{O}}$, E_{H_2} , and E_{O_2} are the calculated total energies of a H_2O , H_2 , and O_2 molecule. ΔZPE and $T\Delta S$ are the changes in zero-point energies and entropy contributions related to the different adsorbed species, calculated as discussed in the “Theoretical Methods” section.

The overpotential, η , which is used as the quantity determining the electrochemical activity, is defined as

$$\eta = \max[\eta_1, \eta_2, \eta_3, \eta_4] \quad (14)$$

with $\eta_i = (\Delta G_i - \Delta G_0)/e$ for $i = 1-4$. Note that $\eta \geq 0$, as the sum of reactions 4–7 gives reaction 3

$$\Delta G_1 + \Delta G_2 + \Delta G_3 + \Delta G_4 = 2\Delta G_{\text{H}_2\text{O}} = 4\Delta G_0 \quad (15)$$

Hence, if the Gibbs free energy of one of the reaction steps is smaller than ΔG_0 , then the Gibbs free energy of one or more of the other reaction steps has to be larger than ΔG_0 .

We calculate the Gibbs free energies 10–13 of the four reactions 4–7 for pristine XN and TM-doped XN, X = Al and Ga, and TM from the 3d series (Sc to Zn in the periodic table). The structures of $*\text{OH}$, $*\text{O}$, and $*\text{OOH}$ for the different (doped) surfaces are shown in Figure S1. For pristine XN, OH and OOH adsorb on top of an X cation, whereas O adsorbs at a hollow site. For TM-doped XN, all stable species adsorb in a position on top of the TM atom. The exception is Zn, which shows no activity toward OH adsorption; instead, OH binds to an X cation. As the Zn dopant is thus totally inert, we omit it from most of the discussion below. We find that the OOH species cannot be stably adsorbed on V, Cr, and Mn dopant atoms, which means that the two reactions 6 and 7 cannot proceed for these systems. Instead, the OOH species spontaneously dissociates into an O species adsorbed on top of the TM atom and a separate OH species adsorbed on a bridge site between the two X cations.

Disregarding these TM dopants, Figure 2a shows the Gibbs free energies 10–13 of the four reaction steps, calculated for the pristine XN monolayers, and the TM-doped XN for the 3d TM atoms Sc, Ti, Fe, Co, Ni, and Cu. The overpotential and the overpotential-determining reaction steps are presented in Figure 2b. All data to these plots are listed in Table S2. Note that the difference between the initial plateau, marked *, and the final plateau, marked O_2 , is fixed to 4.92 eV, because of the sum rule of eq 15. The ΔG staircases can be qualitatively very different for the different TM dopants, and the overpotential-determining reaction step varies. It is then not surprising that large differences in the overpotential are found among these systems.

Pristine AlN and GaN monolayers show similar overpotentials of 0.74 and 0.73 V, respectively. The early TM dopants Sc and Ti lead to considerably higher overpotentials, the late TM dopants Fe and Co give moderately higher overpotentials, and Cu gives a comparable overpotential to the pristine layers. Most interesting is the late TM dopant Ni, which gives a significantly lower overpotential. The low overpotential for the Ni-doped AlN and GaN layers is in fact

comparable to those of the best platinum group TM oxides, for example, RuO_2 with an overpotential of 0.37 V and IrO_2 with 0.56 V.⁵⁹ The latter results have been obtained with slightly different computational methods and settings. However, we can benchmark our method from calculations on hematite.^{8,9} For instance, the hematite (110) surface with an oxygen vacancy concentration of 1.26 vacancies/ nm^2 leads to an overpotential of 0.47 V,⁹ which is in agreement with other computational studies, as well as with experimental data.^{46,61}

Binding Energies of Adsorbed Species. To analyze the trends in the calculated overpotentials, it is helpful to consider the adsorption energies of the different species. The Gibbs free energies of adsorption ΔG_{ADS} , where ADS is the adsorbed species $*\text{OH}$, $*\text{O}$, or $*\text{OOH}$, relative to the clean surface (*) and to H_2 and H_2O , can be straightforwardly obtained from the Gibbs free energies of reactions 10–13

$$\begin{aligned} \Delta G_{*\text{OH}} &= \Delta G_1 \\ &= E(*\text{OH}) - E(*) - E_{\text{H}_2\text{O}} + \frac{1}{2}E_{\text{H}_2} \\ &\quad + (\Delta\text{ZPE} - T\Delta S)_1 \end{aligned} \quad (16)$$

$$\begin{aligned} \Delta G_{*\text{O}} &= \Delta G_1 + \Delta G_2 \\ &= E(*\text{O}) - E(*) - E_{\text{H}_2\text{O}} + E_{\text{H}_2} \\ &\quad + (\Delta\text{ZPE} - T\Delta S)_{1+2} \end{aligned} \quad (17)$$

$$\begin{aligned} \Delta G_{*\text{OOH}} &= \Delta G_1 + \Delta G_2 + \Delta G_3 \\ &= E(*\text{OOH}) - E(*) - 2E_{\text{H}_2\text{O}} + \frac{3}{2}E_{\text{H}_2} \\ &\quad + (\Delta\text{ZPE} - T\Delta S)_{1+2+3} \end{aligned} \quad (18)$$

Note that $\Delta G_{*\text{OOH}}$ can only be calculated for those cases where the OOH species can be adsorbed stably. The Gibbs free energies $\Delta G_{*\text{OH}}$, $\Delta G_{*\text{O}}$, and $\Delta G_{*\text{OOH}}$ for the pristine and the TM-doped AlN and GaN layers are shown in Figure 3. The lower the Gibbs free energy, the stronger the binding of the molecular species to the active site in the monolayer.

Starting with the OH adsorption (black squares in Figure 3), it is found that $\Delta G_{*\text{OH}}$ varies considerably with the TM dopant, where a similar behavior is found for TM-doped AlN (Figure 3a) and GaN (Figure 3b). Along the TM series, $\Delta G_{*\text{OH}}$ decreases strongly from Sc to Ti and increases more gradually from Ti to Cu, where the minimum value is at Ti. Such an increase for late TMs, signaling a decrease in bonding with the adsorbed OH, is consistent with the results found in previous studies.²⁸ $\Delta G_{*\text{OH}}$ is actually negative from Ti to Cr, indicating that OH is strongly bonded to the TM dopant in these systems, and even for Sc, Mn, and Fe, it is barely positive. This is unfavorable for obtaining a low overpotential.

As discussed in the previous section, the ideal Gibbs free energies of reactions 10–13 are ΔG_0 (1.23 eV), eq 9, as this results in a zero overpotential. The deviation of $*\text{OH}$ from ideal adsorption can then be defined as

$$\Delta\Delta G_{*\text{OH}} = \Delta G_{*\text{OH}} - \Delta G_0 = \Delta G_1 - \Delta G_0 \quad (19)$$

Hence, for cases with negative and barely positive $\Delta G_{*\text{OH}}$, $\Delta\Delta G_{*\text{OH}}$ is substantially negative. Because of the sum rule that exists for the reaction Gibbs free energies, eq 15, $|\Delta\Delta G_{*\text{OH}}|$ has to be added to the sum of the remaining three reaction steps, 11–13, which can lead to a substantial overpotential. This is

Figure 3. Gibbs free energies of adsorption, ΔG_{ADS} , for ADS = *OH (black squares), *O (red circles), and *OOH (blue triangles) on TM-doped (a) AlN and (b) GaN monolayers, according to eqs 16–18; the lines are to guide the eye.

clearly visible in the ΔG staircase for Ti in Figure 2, where the first step ΔG_1 goes down. This step in the wrong direction has to be compensated by the remaining three steps, which results in at least one step being significantly larger than ΔG_0 , and a large overpotential (in this case $\eta = (\Delta G_4 - \Delta G_0)/e \approx 2$ V, eq 16). In conclusion, a strongly negative $\Delta\Delta G_{*\text{OH}}$ (strong bonding of the OH species) is detrimental for a low overpotential. This would imply that all early TM dopants from Sc to Fe are less suitable for the OER.

The $\Delta G_{*\text{O}}$ curve in Figure 3 shows qualitatively a similar behavior as the $\Delta G_{*\text{OH}}$ curve. Along the TM series, $\Delta G_{*\text{O}}$ decreases strongly from Sc to V and increases more gradually

from V to Cu. Compared to the $\Delta G_{*\text{OH}}$ curve, the minimum is displaced from Ti to V.

The $\Delta G_{*\text{OOH}}$ curve is remarkably similar in shape to the $\Delta G_{*\text{OH}}$ curve. In fact, subtracting a fixed number from all $\Delta G_{*\text{OOH}}$ values brings the $\Delta G_{*\text{OOH}}$ and $\Delta G_{*\text{OH}}$ curves close. We will discuss this point in more detail below. Meanwhile, it can be deduced from these curves that the OOH species cannot be adsorbed in a thermodynamically stable way on the TM dopants V, Cr, and Mn. The Gibbs free energy of dissociation of *OOH into *O and *OH, all adsorbed on a dopant atom, is given by

$$\begin{aligned}\Delta G_{*\text{OOH}}^{\text{dis}} &= \Delta G_{*\text{OOH}} - \Delta G_{*\text{OH}} - \Delta G_{*\text{O}} = \Delta G_3 - \Delta G_1 \\ &= E(*\text{OOH}) + E(*) - E(*\text{O}) - E(*\text{OH}) \\ &\quad + (\Delta\text{ZPE} - T\Delta S)_{3-1}\end{aligned}\quad (20)$$

If $\Delta G_{*\text{OOH}}^{\text{dis}} < 0$, then an adsorbed OOH species is thermodynamically stable against dissociation into adsorbed O and OH species. For all TM dopants where $\Delta G_{*\text{OOH}}$ can be calculated, we find from Figure 3 that $2.7 \text{ eV} < \Delta G_{*\text{OOH}} - \Delta G_{*\text{OH}} < 3.6 \text{ eV}$. Taking the lower limit of this, it means that $\Delta G_{*\text{O}} > 2.7 \text{ eV}$ for the result of eq 20 to be negative, signaling a thermodynamically stable *OOH species. This is clearly not the case for the V, Cr, and Mn dopants in Figure 3. Moreover, calculation of $\Delta G_{*\text{OOH}}^{\text{dis}}$, eq 20, according to the numbers given in Figure 3 and Table S2, shows that the Ti, Fe, and Co dopants also do not yield a stable *OOH. For all these TM dopants, *O is too stable, and *OOH may dissociate into *OH and *O, all adsorbed on top of a dopant atom.

One could argue that *OOH might be metastable for the Ti, Fe, and Co dopants because the TM dopant atoms are sufficiently far apart for a dissociation into *O and *OH to occur. One may envision another dissociation reaction with the O species adsorbed on a TM dopant atom, and the OH adsorbed on the adjacent dopant-free part of the surface, see Figure S1d–f. The Gibbs free energy of dissociation, $\Delta G_{*\text{OOH}}^{\text{dis}}$, of that reaction can be estimated from eq 20 using $\Delta G_{*\text{OH}} = \Delta G_1$ of the pristine AlN or GaN, see Table S2. However, even

Figure 4. Gibbs free energy difference, ΔG_{23} , on TM-doped (a) AlN and (b) GaN according to eq 21, the dashed horizontal lines indicate the ideal value $2G_0 = 2.46 \text{ eV}$. The Gibbs free energy difference $\Delta\Delta G_{*\text{O}}$ on TM-doped (c) AlN and (d) GaN according to eq 23, the dashed horizontal lines indicate the optimal value of 0 eV. The lines are to guide the eye.

in that case, we find $\Delta G_{*OOH}^{dis} > 0$ for the Ti, Fe, and Co dopants, indicating that $*OOH$ is thermodynamically unstable for these dopant atoms. Nevertheless, in our structural optimization, we do find $*OOH$ structures that form local minima, that is, structures of OOH adsorbed on Ti, Fe, and Co dopants that are metastable. This is in contrast with V, Cr, and Mn dopants, where no such structures are found.

Only the late TM dopants Ni and Cu give $\Delta G_{*OOH}^{dis} < 0$, eq 20, which implies a thermodynamically stable adsorbed OOH species. As discussed above, a strong adsorption of OH would lead to a substantial overpotential. In the Ni and Cu cases, $\Delta\Delta G_{*OH} > 0$, eq 19, indicating an OH species that is not adsorbed strongly. In fact, the bonding of OH to Ni or Cu is relatively weak, which implies a minimum overpotential $\eta_1 = \Delta\Delta G_{*OH}/e$ resulting from this first reaction step, eq 14 and Figure 2a. Of course, still larger overpotentials may, in principle, follow from the subsequent reaction steps 5–7.

Next, we zoom in on the Gibbs free energy difference that reflects the difference in bonding of OH and OOH species to the surface

$$\Delta G_{23} = \Delta G_{*OOH} - \Delta G_{*OH} = \Delta G_2 + \Delta G_3 \quad (21)$$

see eqs 11 and 12. This quantity thus represents the Gibbs free energy associated with the two reactions 5 and 6, that is, the two middle steps in the staircases of Figure 2a. The calculated values for the TM-doped systems are shown in Figure 4a,b for the AlN and GaN system, respectively.

To avoid the two reaction steps 5 and 6 contributing to an overpotential, ΔG_{23} should ideally be equal to $2\Delta G_0 = 2.46$ eV, see eqs 9 and 14,⁶² for all TM-doped systems, as indicated by the dotted horizontal lines in Figure 4a,b. In general, however, ΔG_{23} is significantly higher than the ideal value of 2.46 eV and is different for the different TM dopants. For most TM dopants, we find ΔG_{23} to be between 3.10 and 3.60 eV (Figure 4a,b), which is consistent with the range found in TM oxides and in TM-doped graphene.^{27,28,62} The minimum overpotential resulting from the two reaction steps 5 and 6 is then

$$\eta_{23} = (\Delta G_{23} - 2\Delta G_0)/(2e) \quad (22)$$

On the basis of the data for all TM-doped systems shown in Figure 4a,b and eq 22, η_{23} mostly ranges between 0.3 and 0.6 V. To decrease this number, one should increase the bonding of OOH to the TM with respect to the TM/ OH bonding, eq 21. This is observed in the Ni-doped systems, where for Ni/AlN and Ni/GaN, we find $\eta_{23} = 0.11$ and 0.21 V, respectively. These values are close to a perfect OER catalyst with an overpotential of zero.

The quantity η_{23} gives a lower bound to the overpotential in case $\Delta G_2 = \Delta G_3$. If $\Delta G_2 \neq \Delta G_3$, one should also consider the adsorption strength of the O species with respect to the average of the OH and OOH species

$$\begin{aligned} \Delta\Delta G_{*O} &= \Delta G_{*O} - \frac{1}{2}(\Delta G_{*OH} + \Delta G_{*OOH}) \\ &= \frac{1}{2}(\Delta G_2 - \Delta G_3) \end{aligned} \quad (23)$$

$\Delta\Delta G_{*O}$ can be derived from Figure 3 as the difference between the Gibbs free energy curve of $*O$ and the average of the $*OH$ and $*OOH$ curves. The minimum overpotential from the two reaction steps 5 and 6 is then

$$\min[\eta_2, \eta_3] = \eta_{23} + |\Delta\Delta G_{*O}|/e \quad (24)$$

see eqs 21 and 23 and Figure 4. Ideally, $\Delta\Delta G_{*O}$ should be as close to zero as possible. Figure 4c,d show that $\Delta\Delta G_{*O}$ starts strongly positive for Sc and then becomes negative, before becoming positive again for Cu. For most TM dopants, $|\Delta\Delta G_{*O}|$ is substantial. Of the late TM dopants, the exceptions are Ni-doped AlN and GaN, where we obtain the relatively small values $\Delta\Delta G_{*O} = -0.12$ and -0.16 eV, respectively.

In summary, analyzing the Gibbs free energies associated with the bonding of the different adsorbents shows how in particular the Ni-doped systems lead to a low overpotential. First of all, OH is bonded too strongly to the early TM dopants in the series Sc to Fe, indicated by $\Delta\Delta G_{*OH} < 0$, eq 19, which leads to a substantial overpotential. In addition, for the TM dopants in the middle of these series, V, Cr, and Mn, the O species is bonded so strongly that $*OOH$ is unstable with respect to decomposition into $*OH$ and $*O$. V, Cr, and Mn dopants should therefore show no activity at all for the OER. For the late TM dopants Co to Cu, Ni shows values ΔG_{23} , eq 21, that are close to the optimal value $2\Delta G_0$, whereas the other dopants show higher values. In addition, the value of $\Delta\Delta G_{*O}$, eq 23, is optimal for the Ni dopant.

One can try to relate ΔG_{*OOH} and ΔG_{*O} to ΔG_{*OH} by linear scaling relations, as suggested in the literature.^{28,59,62} However, Figure 4 shows that such scaling relations work poorly in the present case.

Electronic Structure of Adsorbed Species. We now focus on the electronic structures of the TM-doped AlN and GaN layers to see whether the trends found in the binding energies can be explained from the electronic structures. The spin-polarized PDOS of two examples are shown in Figure 5,

Figure 5. Spin-polarized PDOS of (a) Ti-doped AlN and (b) Ni-doped AlN. The highest occupied state is set to 0 eV.

an early TM dopant (Ti) and a late TM dopant (Ni), both in AlN. PDOSs of the full 3d TM-doped XN series, TM = Sc to Zn, X = Al and Ga, are given in the Supporting Information in Figures S2 and S3. In addition, orbital-resolved PDOSs for all these cases are given in Figures S4 and S5. It is clear from these figures that the PDOSs of spin-up and spin-down states are different for all TM-doped XN, except for Sc and Zn dopants.

Therefore, with the exception of the latter two dopants, TM doping leads to substantial magnetic moments, which to a significant part are carried by the d states on the TM dopant atoms. Indeed, for the early TM dopants in particular, the PDOS corresponding to the 3d states consists of sharp peaks (Figures S2b–d, S3b–d), signaling that hybridization of these states with the XN environment is small. Hybridization increases slightly going down the TM series, indicated by some of the peaks attaining a mixed TM–nitrogen character (Figures S2e–i, S3e–i) and by a bonding/antibonding splitting in some cases.

Ignoring this hybridization, the nominal charge of a TM substitutional dopant atom in the XN lattice is 3+. To set up a simple electron counting argument, we assume that all (neutral) TM atoms have a $4s^23d^n$ configuration, and by embedding them in the XN lattice, two electrons are donated by the TM 4s shell and one electron is donated by the 3d shell to arrive at a charge 3+. This would then mean that the TM dopant atom has configuration $4s^03d^{n-1}$, where n is the number of d electrons of the neutral atom. The PDOSs shown in Figures 5, S4b and S4h are indeed consistent with d^1 for the Ti dopant, and with d^7 for the Ni dopant. In fact, most of the PDOSs of the Supporting Information Figures S2–S5 comply with the TM configuration d^{n-1} and thus with a nominal charge of 3+. The exceptions are the late TM dopants Cu and Zn, which have configurations d^n , that is, d^9 and d^{10} , respectively (Figures S4i,j and S5i,j), indicating a nominal charge of 2+.

Most prominent in Figure 5 is that the d states of Ti are in energy more than 2 eV above the valence band of AlN, whereas the d states of Ni largely overlap with the valence band. One therefore expects the d^1 state of Ti to be more reactive toward adsorption of an electron-accepting OH species than either the AlN substrate or the Ni d states. The d states go down in energy along the TM series from Ti to Zn, see Figures S2 and S3; hence, the reactivity should go down. Indeed, this can be seen as an increase in ΔG_{*OH} along the TM series in Figure 3.

Adsorption of the O species requires two electrons from the substrate instead of only one, as in the case of OH species. One expects adsorption to be strongest for a TM dopant with d^2 configuration, which is the TM dopant V. The ΔG_{*O} curve in Figure 3 shows that this is indeed the case.

To clarify why doping by Ni is particularly advantageous for obtaining a low overpotential, we consider the spin state of the TM-doped XN layers. If the TM d-levels were purely atomic, then Hund's (first) rule would predict a high-spin state for all dopant atoms. On the basis of the electron-counting argument outlined above, Hund's rule would give for the 3+ TM dopants Sc to Fe a spin $(n - 1)\frac{1}{2}$, for the TM dopants Co and Ni a spin $(10 - n + 1)\frac{1}{2} = \frac{4}{2}$ and $\frac{3}{2}$, respectively, and for the 2+ TM dopants Cu and Zn a spin $\frac{1}{2}$ and 0, respectively. Hybridization between the TM and XN states gives a ligand field that lifts the degeneracy of the d-levels. For instance, it can be observed in Figure 5a that the peaks of the spin-up d states of Ti are distributed over a range from -0.2 to 2.3 eV, which illustrates that this splitting is easily of the order of several eV's. If ligand-field splitting would be the dominant energy scale, this would force the TM-doped systems into low-spin states.

The calculated total magnetic moments of the TM dopants are listed in Table 1. All TM dopant atoms are found in their

Table 1. Calculated Total Magnetic Moments (in μ_B per Supercell) of TM-Doped XN, X = Al and Ga^a

system	Sc	Ti	V	Cr	Mn	Fe	Co	Ni	Cu	Zn
nothing adsorbed	0	1	2	3	4	5	4	3	1	0
OH adsorbed	0	0	1	2	3	4	5	4	1	/
O adsorbed	0	0	0	1	2	3	0	1	1	/
OOH adsorbed	0	0	/	/	/	4	5	2	1	/

^a/ means that the intermediates do not adsorb stably or metastably on the dopants.

high-spin state predicted by Hund's rule, see the first line in Table 1. It demonstrates that the energy scale associated with Hund's rule still prevails over the ligand-field splitting. The magnetic moments of the late TM dopants are not completely localized on the TM atoms because of the increased hybridization with the XN lattice. The components of the magnetic moments projected on the TM site are given in Table S3 in the Supporting Information.

A similar analysis of the d-level spectrum and the associated spin states can be performed with the OH, O, or OOH species adsorbed on the TM dopant atom. The calculated orbital-resolved PDOSs are given in the Supporting Information, Figures S6–S8, and the calculated total magnetic moments are given in Table 1. Comparing the first two rows in Table 1, one observes that the entries of the second row are shifted one element to the right, as compared to the first row. Therefore, it seems that adsorption of OH decreases the number of electrons on the TM dopant by 1, thus changing its configuration to d^{n-2} , while the systems with OH adsorbed still obey Hund's rule, and are found in their high-spin state. Exceptions are Cu, which remains in a d^9 configuration even with OH adsorbed, and the trivial case Sc, which remains in a d^0 configuration.

Applying the same reasoning to an adsorbed O atom, one may expect that adsorption of O decreases the number of electrons on the TM dopant by 2, thus changing its configuration to d^{n-3} . If Hund's rule applies, resulting in high-spin states, then the third row in Table 1 could be obtained from the second row by again shifting it one element to the right. This is indeed the case for all TM dopants up to Fe. As before, Cu remains in a d^9 configuration even with O adsorbed. Remarkably, for O adsorption on the late TM dopants Co and Ni, the total magnetic moments for O–Co/XN and O–Ni/XN are 0 and $1 \mu_B$, respectively, see Table 1 and Figure 6, implying that the preferred configuration is the low-spin state.

Figure 6. Schematic ligand-field splitting of Ni d-levels for Ni-doped XN, X = Al and Ga. The pristine and OH-adsorbed systems are in a high-spin state, whereas the O-adsorbed and OOH-adsorbed systems are in a low-spin state, see Table 1.

The total magnetic moment and the energy difference $\Delta E(^*O)$ between the high-spin and the low-spin states of O–Co/XN and O–Ni/XN are listed in Table S4. The high-spin state of these systems is 0.5–0.6 eV higher in energy than the low-spin state (with the exception of O–Ni/AlN, where the high-spin state does not give a stable adsorption of O on Ni). Assuming that both the OH and OOH species adsorb in a high-spin state, as is the case for most TM dopants, then stabilization of the low-spin state of an adsorbed O species results in a $\Delta\Delta G_{*O}$, eq 23, that is strongly negative, which leads to a substantial overpotential, see eq 24 and Figure 2. Indeed, it can be observed in Figure 4c,d that this is the case for $\Delta\Delta G_{*O}$ of Co-doped AlN and GaN. Remarkably, the stable low-spin state of the O–Ni/XN systems does not cause a similarly negative $\Delta\Delta G_{*O}$ and a high overpotential. This has to do with the stable spin state of an adsorbed OOH species.

If adsorption of OOH is similar to that of OH, then the electron count gives a d^{n-2} configuration for both cases, and Hund's rule should give an identical high-spin state for both cases. Judging from the magnetic moments listed in Table 1, this is indeed the case for most of the TM dopants where OOH can be stably adsorbed. The notable exception is Ni. Here, the adsorbed OOH remains in a low-spin state, similar to adsorbed O, and does not switch to a high-spin state similar to adsorbed OH, as it does for all other TM dopants. Figure 6 visualizes the assembly of spin states that is unique for the Ni dopant. As the low-spin states of both the adsorbed O and the OOH species on Ni are stabilized, this leads to a decrease of ΔG_{23} (eq 21), as well as $|\Delta\Delta G_{*O}|$ (eq 23), see Figure 4, which then yields a low overpotential.

SUMMARY

In summary, we have investigated the OER of water splitting on first-row TM-doped AlN and GaN 2D monolayers by DFT calculations. The binding strength of OH or O, overpotential, overpotential-determining reaction steps, and spin states of *OOH of the TM-doped systems are summarized in Figure 7. We find that the Ni-doped AlN and GaN monolayers single out as most favorable for the OER, as they lead to small calculated OER overpotentials of 0.38 and 0.37 V, respectively.

Early TM dopants are not suited for an efficient OER because in the first reaction step of the OER, they bind the OH species too strongly. In fact, V, Cr, and Mn dopants should show no activity for the OER at all because additionally in the second OER step, they bind the O species so strongly that the

third step, conversion to OOH, becomes impossible. The latter becomes feasible for late TM dopants, but for Fe and Co, it is still energetically costly because of the strong binding of the O species. Elements at the end of the TM series, Cu and Zn, show little or no activity. They bind adsorbants weakly, and their d-shells do not participate in this bonding.

Ni is unique as a dopant in these systems, as all four reaction steps of the OER are relatively close to their optimal values, meaning that the adsorption energies of the three intermediate-adsorbed species, OH, O, and OOH, are close to optimal. For instance, the Gibbs free energy difference between OH and OOH adsorbed on the Ni dopant is ~ 2.7 eV, which is significantly lower than ~ 3.3 eV found for adsorption on the other dopants. The latter value is close to that found more generally for other compounds. In contrast, the value for Ni is rather close to the ideal value of 2.46 eV for a perfect catalyst.

The numbers correlate with the spin states of the TM dopants. In most cases, the high-spin state is preferred both for the pristine TM-doped AlN and GaN, as well as for all intermediate species involved in the OER, that is, OH, O, and OOH adsorbed on the TM dopant. However, for the Ni dopant, the low-spin state is stabilized both for the adsorbed O, as well as for the adsorbed OOH species (whereas the high-spin state is most stable for adsorbed OH and for the pristine dopant). This stabilization leads to a low overpotential in the Ni-doped AlN and GaN. Such a change in spin state adds a degree of freedom to optimize the overpotential required for the OER.

ASSOCIATED CONTENT

Supporting Information

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acs.jpcc.9b06704.

Zero-point energy and entropic correction; optimized structures of TM-doped AlN and GaN with/without adsorbants; Gibbs free energies; spin-polarized PDOS of TM-doped AlN and GaN; spin-polarized PDOS of TM-doped AlN and GaN with adsorbed OH, O, and OOH; magnetic moments of TM dopant ions in AlN; high-spin versus low-spin states; GGA + *U* calculations for Co/XN and Ni/XN; and comparison of the results with those of the standard GGA calculations (PDF)

AUTHOR INFORMATION

Corresponding Author

*E-mail: A.Bieberle@diffier.nl.

ORCID

Qihua Liang: 0000-0002-5436-5203

Xueqing Zhang: 0000-0002-7310-3858

Anja Bieberle-Hütter: 0000-0001-8794-9312

Notes

The authors declare no competing financial interest.

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Figure 7. Binding strength of OH or O, overpotential, overpotential-determining reaction steps and spin states of *OOH of the TM-doped systems.

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